

ATLAS pixel 3-D design using two tiers of electronics

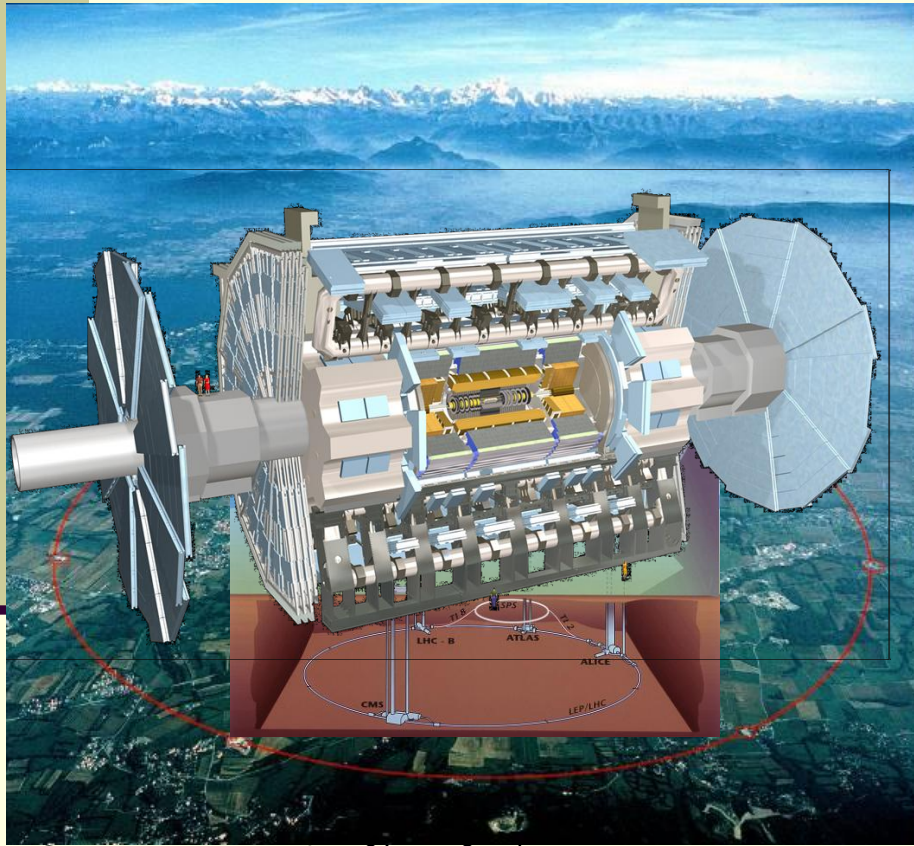
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Hybrid Pixels Detector for LHC/SLHC at CERN



- Hybrid Pixels Detector of ATLAS/LHC
 - Like a big camera with a 1.7 m² area and 80 Million of Pixels with a snapshot every 25ns
- Hybrid Pixels Detector of ATLAS/SLHC
 - More luminosity, more pixels more ionizing particles, more ... !!!

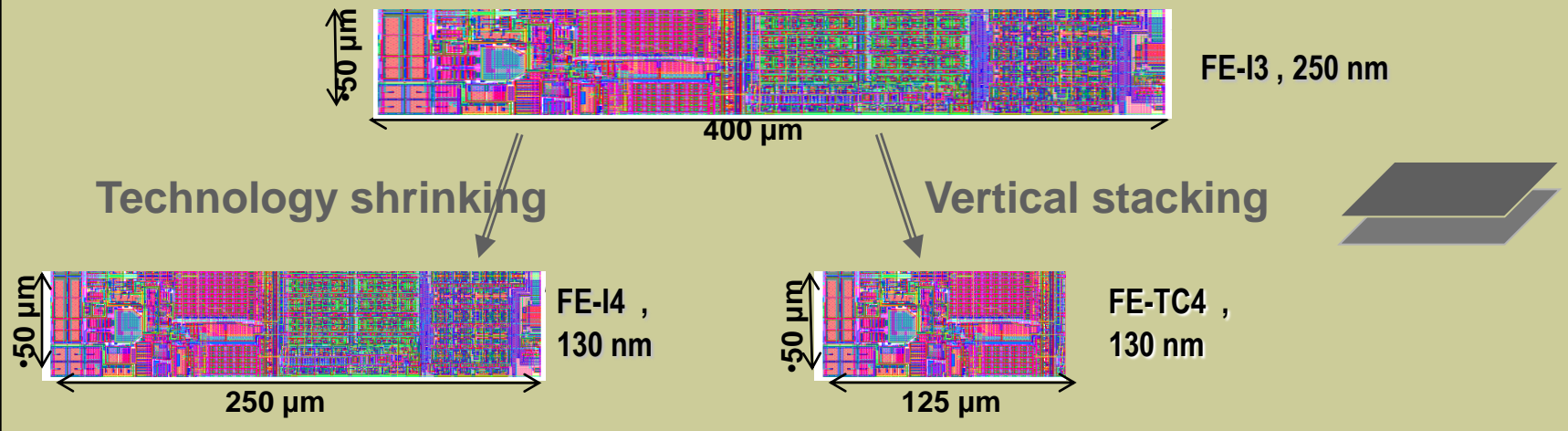
LHC : Luminosity of $10^{34} \text{ cm}^{-2} \cdot \text{s}^{-1}$

SLHC expected 10 times more !!!

3-D motivations for ATLAS read-out chip upgrades

- Improve spatial resolution
 - Deal with an increasing counting rate
- } → Decrease pixel size

3D pixel road map (A.Rozanov, ATLAS-France Paris, June 22, 2009) :



3-D benefits :

- Pixel size reduction
- Functionalities splitting
- Technologies mixing

Context of ATLAS 3-D beginning...

- Objectives :

- Design a 3-D pixel based on the FE-I_4 pixel by splitting its functionalities into two parts :
 - one for the analogue functions,
 - one for the digital parts.

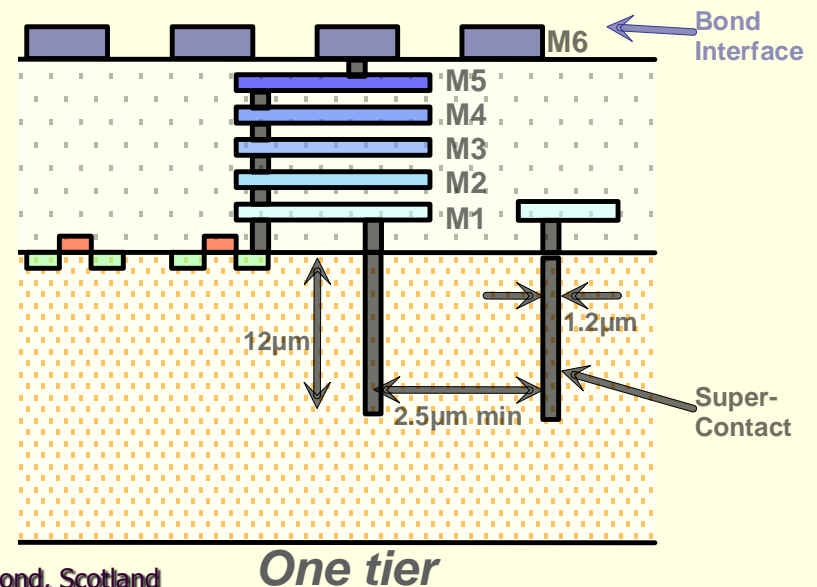
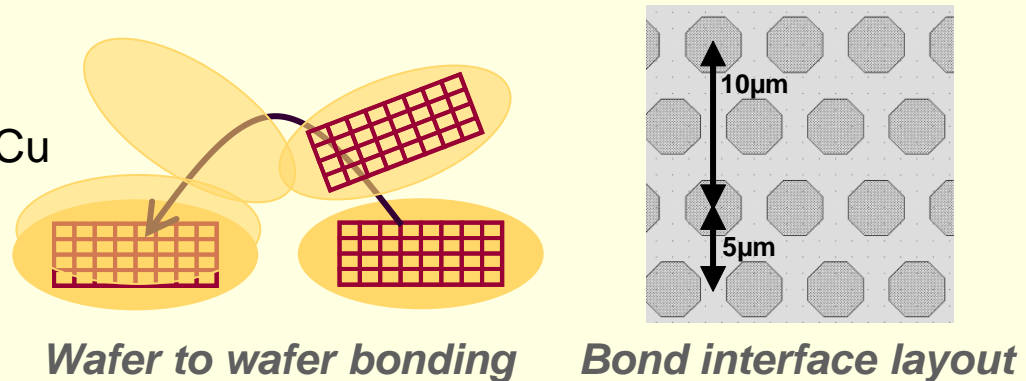
- Context :

- 2009 : First MPW run for High Energy Physics organized by FNAL with a consortium of 15 institutes (France, Germany, Italy, Poland and United-States)
- The proposed 3-D process combines :
 - **CHARTERED 130nm technology**
 - **TEZZARON 3D technology**

Tezzaron-Chartered 3D technology

Main characteristics :

- **2 wafers** (tier 1 and tier 2) are stacked **face to face** with Cu-Cu thermo-compression bonding
- **Via First** technology : **Super-Contacts** (Through Silicon contacts) are formed before the BEOL of Chartered technology.
- Wafer is **thinned** to access Super-Contacts
- Chartered technology limited to **5 metal levels**
- **Back-side metal** for bonding (after thinning)



3D project steps

Submission / Test :

March 08 / Summer 08

The base is the **FEI4_P1** design (pixel read-out prototype chip for ATLAS upgrades) :

- 14x61 "analogue" pixel matrix
- Pixel size : 50x166 μ m
- 8 metal levels
- IBM 130nm



3D project steps

Submission / Test :

FEI4_P1 design : IBM 130nm, 8 metals

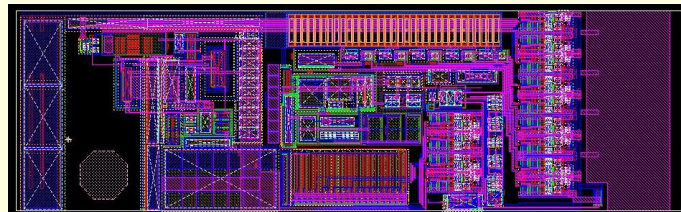
March 08 / Summer 08

→ Translation into **2D CHARTERED** technology :

February 09 / April 09

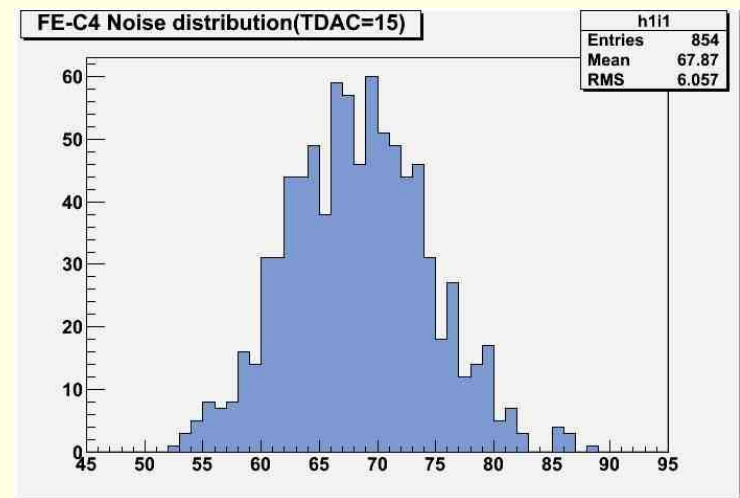
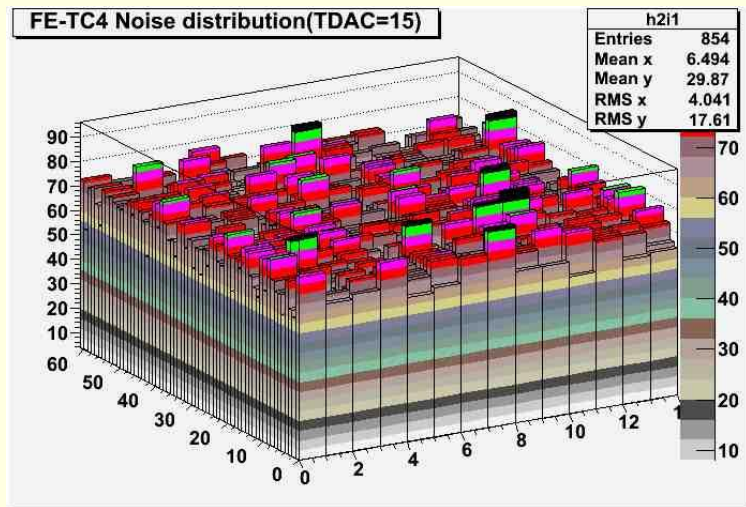
FEC4_P1 circuit

- 14x61 "analogue" pixel matrix
- Pixel size : 50x166 μ m
- 8 metal level
- Pixel structure : identical to FEI4
(due to schedule no optimization has been done)
- Objectives : test Chartered technology
(functionalities, performances, radiation...)



FEC4_P1 test results

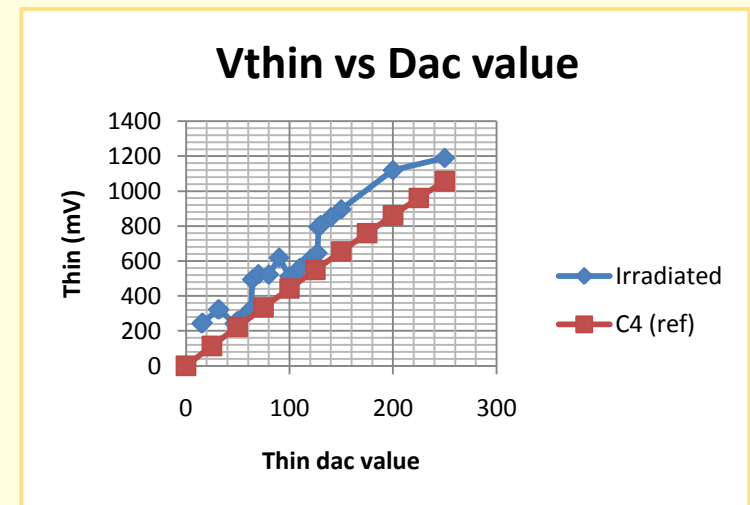
- Even with no optimization for Chartered technology, main results are equivalent to IBM ones :
 - Threshold min around 1100 e-
 - Un-tuned threshold dispersion 200 e-
 - Noise lower than 80 e-



FEC4_P1 test results

- Irradiation performed at CERN/PS facility (24 GeV protons) up to 400 MRad
 - Problem discovered after 160 MRad on latches (output tends to be blocked in "1" state)
 - Difficult to work with the circuit by after
 - Problem reproduced in simulation "corners"
 - ... but

Analog is still working even with increased of noise :
250 e- (threshold dispersion is meaningless)



3D project steps

Submission / Test :

FEI4_P1 design : IBM 130nm, 8 metals

March 08 / Summer 08

→ **FEC4_P1** circuit : **2D** Chartered, 8metals

February 09 / April 09

↓
First **3D** design (MPW organized by FNAL) :
FETC4_P1 project

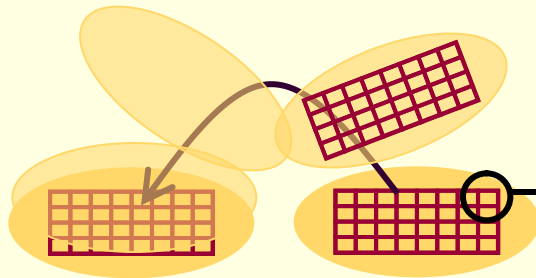
July 09 / Summer 10

- Chartered (5 metal levels) + Tezzaron
- One Tier for the analogue pixel part :
 - 14x61 pixel matrix
 - Pixel size : 50x166µm
- One Tier for the digital part
 - Two versions have been designed : one dedicated for test, one “FEI4-like”.



Chartered-Tezzaron MPW run

2 identical wafers are stacked \Rightarrow Tier 1 and Tier 2 are in the same reticle.



Chartered reticle :
 26mm x 31mm
 shared between all
 participants

| TX1 | TY1 | TY2 | TX2 |
|-----|-----|-----|-----|
| A1 | B1 | B2 | A2 |
| C1 | D1 | D2 | C2 |
| E1 | F1 | F2 | F2 |
| G1 | H1 | H2 | G2 |
| J1 | K1 | K2 | J2 |

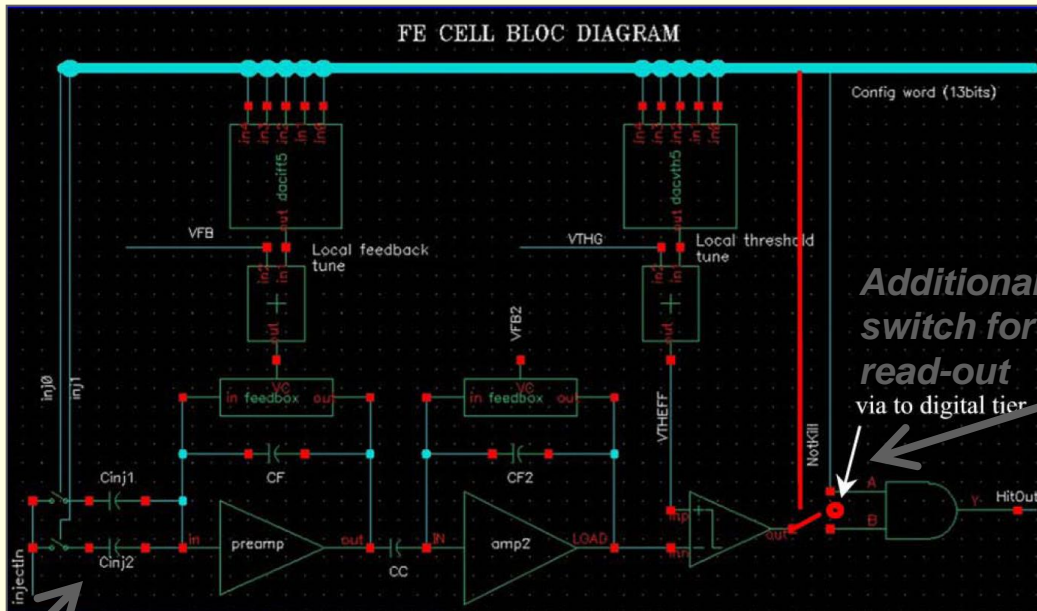


4 sub-reticles for ATLAS/SLHC chips projects : FE_TC4_P1 + OmegaPix

- **C1, D1 = analog tier FE-TC4-AE + analog OmegaPix**
- **C2 = first version for digital tier (dedicated for test) : FE-TC4-DS**
- **D2 = second version for digital tier : FE-TC4-DC read-out structure “FEI4-like”+ digital OmegaPix**

FE-TC4-AE analogue tier

- Based on FEC4_P1 chip + all adds for 3D connection



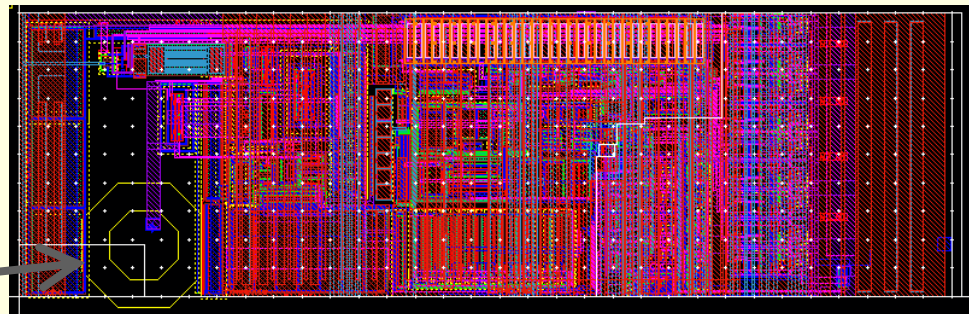
Additional switch for read-out via to digital tier

2 possible ways for discriminator output read-out:

- With the simple read-out part existing yet into the pixel
- With the tier 2 (via the Bond Interface)

Input signal from sensor via the Super-Contacts

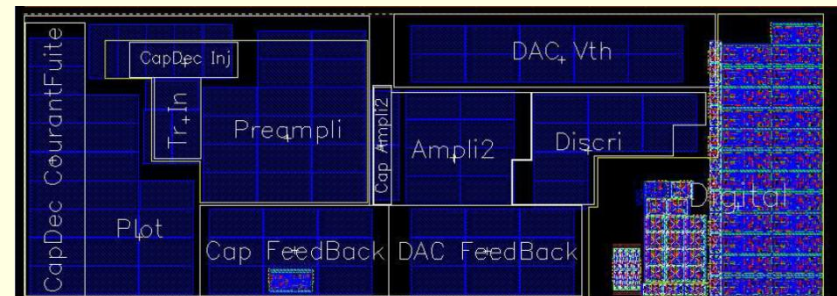
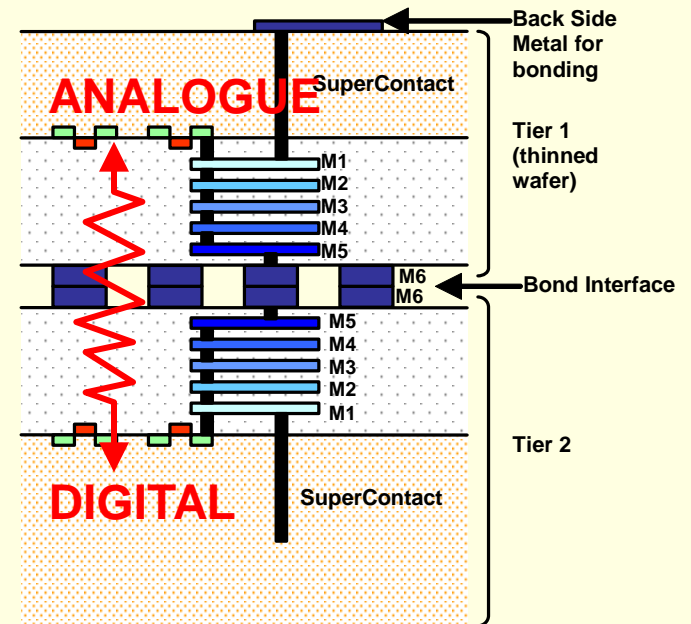
Bonding pad in Back-side metal



June 6-11, 2010, Loch Lomond, Scotland

FE-TC4-DS digital tier for test : parasitic coupling study between tiers

- Analogue tier and digital tier are face to face (sensitive part facing digital part).
- FE-TC4-DS : dedicated for parasitic coupling studies between the 2 tiers.
- 3 functions :
 - Read the discriminator output
 - Generate noise (digital commutations) in front of 11 specific areas of the analogue pixel (preamplifier, feed-back, amplifier2, DAC...)
 - Test different shielding configurations.

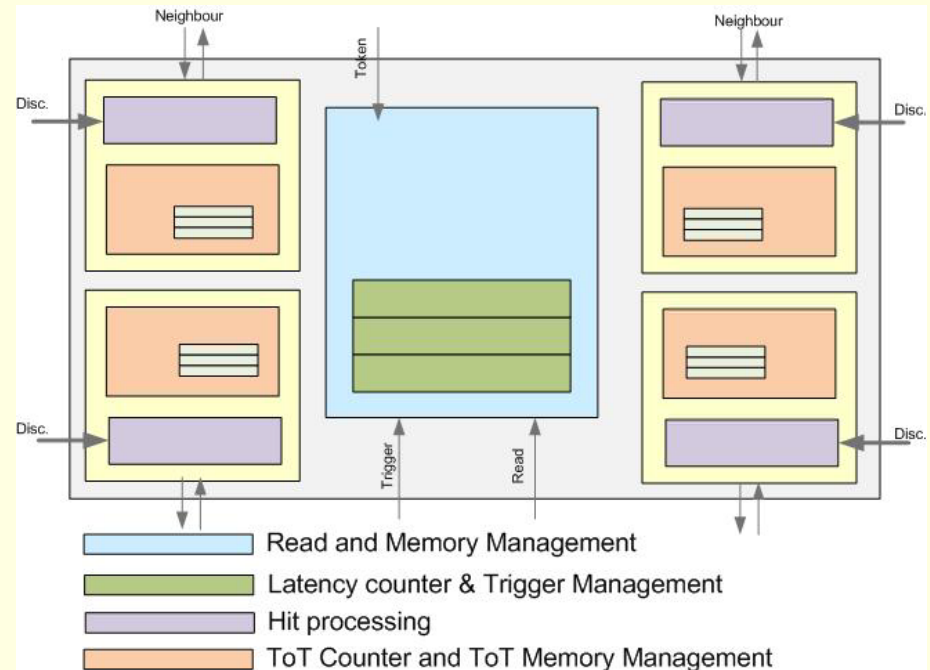


Analogue pixel layout : 11 specific areas

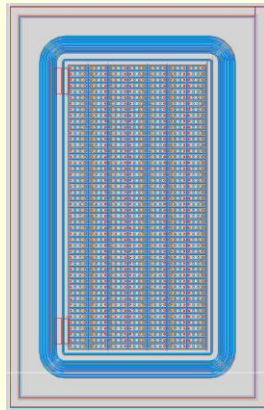
FE-TC4-DC digital tier : complex read-out chip

Read-out chip similar to FE-I4
project :

- **4-pixel region :**
 - 61 pixels/ column => implies 31 '4-pixel' regions plus 2 dummy pixels per double-column.
- **Simplified periphery and read-out control logic :**
 - Some signals are provided from the outside (data read-out signals, signals for pixel hits communication to the periphery...

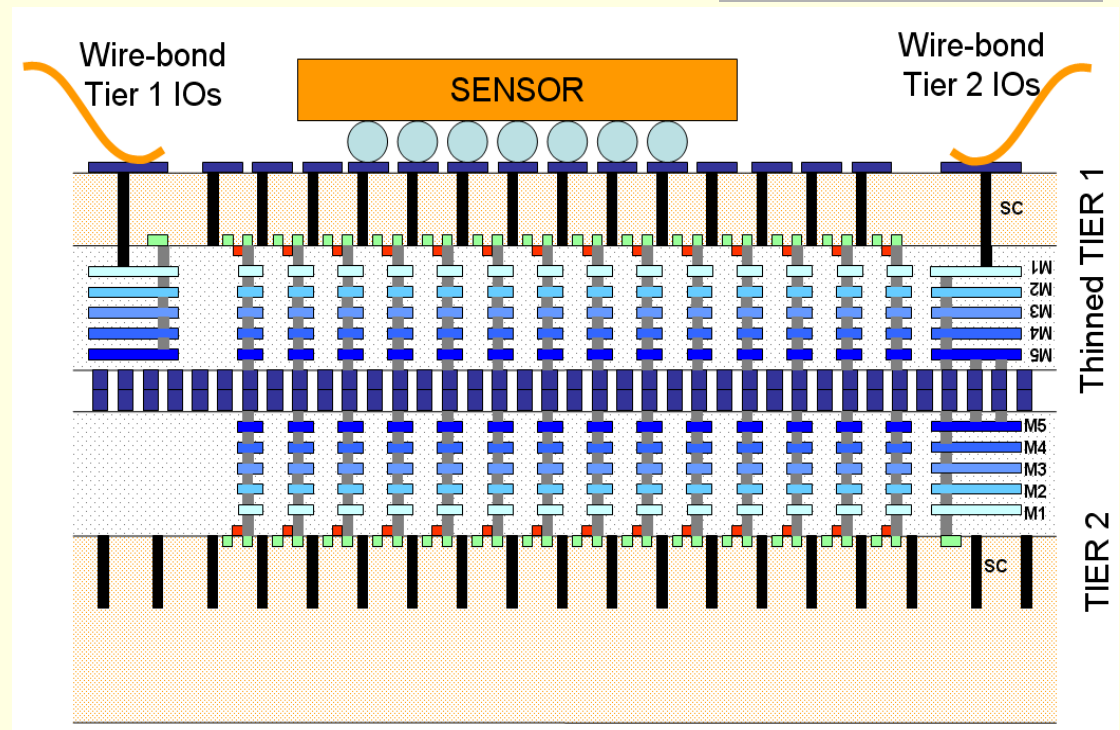


Final assembly (soon...)



Sensor layout :

Anna Macchiolo,
Max-Planck-Institut für Physik,
Munich



Bonding foreseen to be done at IZM (Berlin) as for ATLAS modules
Due to geometric constraints, sensor matrix is reduced :

- Sensor matrix : 7 columns of 48 pixels
- Tier 1 and Tier 2 matrix : 14 columns of 61 pixels

FE-TC4-P1 test results

- The submission of this first 3D MPW run organized by FNAL has encountered a lot of problems :
 - Difficulties for the establishment of a good layout frame reticle according to all requirements of Tezzaron and Chartered,
 - software development or adjustment to well considered all added 3D layers,
 - software limitations for checks,
 - ...
 - Long delay...

- But tests are expected for this summer ...

3D project steps

Submission / Test :

FEI4_P1 design : IBM 130nm, 8 metals

March 08 / Summer 08

→ FEC4_P1 circuit : 2D Chartered, 8metals

February 09 / April 09

↓ FETC4_P1 circuits : 3D first prototype

July 09 / Summer 10

↓ Second 2D prototype : **FEC4_P2** circuit

November 09 / January 10

- Chartered (8 metal levels)
- Based on FEC4_P1 circuit, plus :
 - Optimization of transistors
 - New latches for irradiation tests
 - New PadRing strategy and ground/substrate separation



3D project steps

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July 09 / Summer 10

↓ **FEC4_P2** circuit : 2D Chartered, 8 metals

November 09 / January 10

↓ **FEC4_P3** : Third 2D Chartered prototype

September 10 / End of 10

- Chartered (8 metal levels but only 5 are used)
- Smaller pixel size : 50µm x 125µm
- Design of new sub-circuits and functionalities :
 - Current Reference
 - Analogue multiplexor
 - PLL
 - Triple redundancy



3D project steps

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November 09 / January 10

↓ **FEC4_P3** circuit : 2D Chartered, 8 metals

September 10 / End of 10

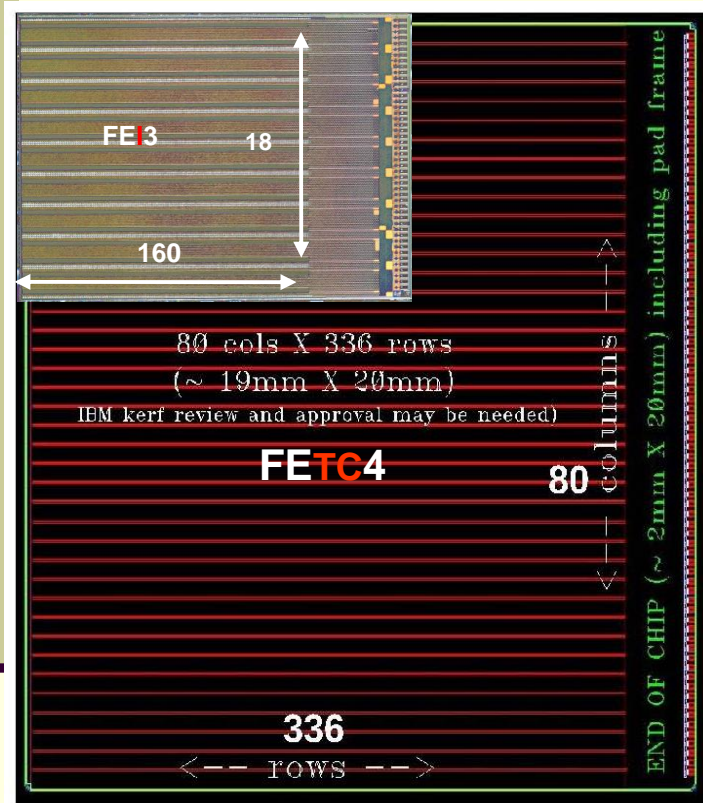
↓ **FETC4_A** design : Second/last 3D design

Begin of 11

- Chartered (5 metal levels) + Tezzaron
- Pixel size : 50µm x 125µm
- Complete functionalities will be implanted on analogue and digital Tiers.



The **FETC4** ATLAS chip



- **FETC4_A**, run 3D Tezzaron-Chartered technology :
 - Very large matrix size : 336 x 80 pixels
Chip size of 18.8 x 20.1 mm.
1.95 mm End Of Column size.
 - Small pixel size : 125 μ m x 50 μ m
 - Bump bond pads compatible with 250 μ m sensor pitch (FEI4_A project)
 - The **FETC4** chip is a FE_I4 blocks reuse, compatibility with FEI4 chip for sensors, bump bonding , module/stave integration, testing tools, software, mechanics

3D IC Consortium

Conclusions and future plans

- Benefits of 3D technology for hybrid pixel detectors :
 - Pixel size reduction
 - Technologies mixing
 - More functionalities can be implemented in front of the analogue pixel
 - Since 2 years
 - A 3D prototype, in Tezzaron-Chartered technology, was designed and submitted, as a test bench for this technology, in framework of ATLAS pixel upgrade for higher luminosities.
 - 2D prototyping blocks, in Chartered technology only, were designed and tested to more quickly help the 3D approach.
- Future Plans:
 - Prototyping blocks in 2D Chartered in Summer (e.g. FEND, CREF, CLKGEN, new LVDS...) placed into the FEC4_P3
 - Tests will be performed on FETC4_AEDS (DC) and on 3D test structures.
 - FEC4_P2 chip (transistor optimization and few minor corrections) is under test, and under radiation at CERN/PS.
 - Start working to design a full scale FETC4_A